



80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8 (SWP) (Type Q)

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	$17m\Omega @ V_{GS} = 10V$	53.7A
00 V	$23.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	44.3A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

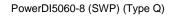
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Additional Tin-plated on Sidewall Pads for Optical Solder Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

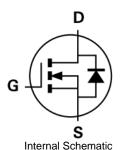
Mechanical Data

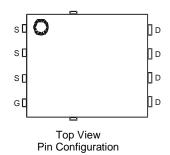
- Case: PowerDI[®]5060-8 (SWP) (Type Q)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 <a>§3
- Weight: 0.097 grams (Approximate)





Top View Bottom View





Ordering Information (Note 4)

Τ			
	Part Number	Case	Packaging
	DMTH8012LPSW-13	PowerDI5060-8 (SWP) (Type Q)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Oll = Manufacturer's Marking
TH8012LSW = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	80	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	10.3 7.3	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I _D	53.7 38	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	69	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	I _{SM}	80	Α	
Avalanche Current, L=0.1mH		I _{AS}	11.6	A
Avalanche Energy, L=0.1mH		E _{AS}	6.7	mJ

Thermal Characteristics

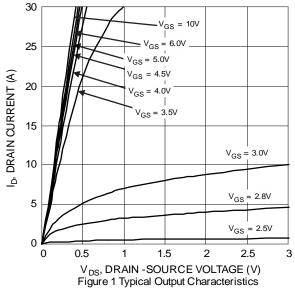
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	49	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P _D	83.3	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.8	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

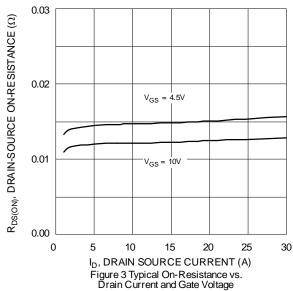
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

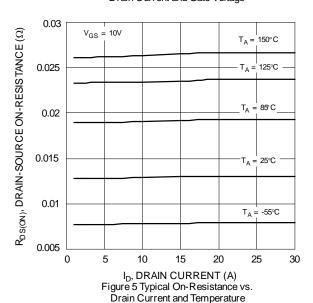
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 64V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	=	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		-	14	17	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialit-Source Off-Nesistance	R _{DS(ON)}	-	16.5	23.5	11122	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	-	0.9	1.2	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1949	-		$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	177	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	10	-			
Gate Resistance	R_g	-	0.7	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	=	15	-		V _{DS} = 40V, I _D = 12A	
Total Gate Charge (V _{GS} = 10V)	Q_g	=	34	-	nC		
Gate-Source Charge	Q_{gs}	-	6	ı	IIC		
Gate-Drain Charge	Q_{gd}	-	4.5	-			
Turn-On Delay Time	t _{D(ON)}	-	4.9	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{g} = 1.6\Omega$	
Turn-On Rise Time	t _R	=	3.8	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	=	16.5	-			
Turn-Off Fall Time	t _F	=	3.5	-			
Body Diode Reverse Recovery Time	t _{RR}	-	30.2	-	ns	I _F = 12A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	-	34.6	-	nC	= 12A, α//αι = 100A/μS	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:



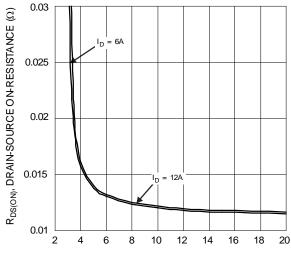






20 V_{DS} = 5.0V 15 T_A = 150°C T_A = 85°C T_A = 25°C T_A = -55°C

 V_{GS} GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

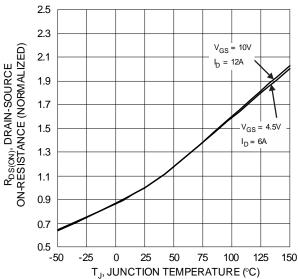
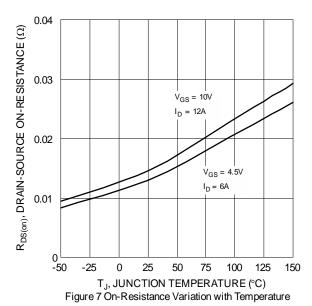
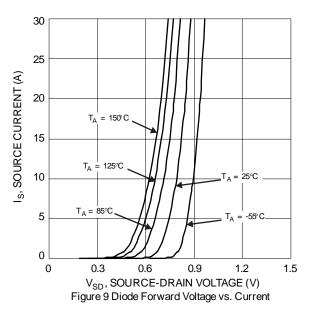
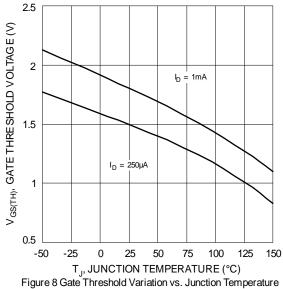


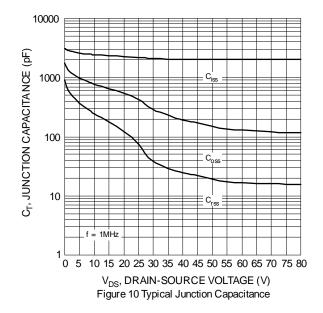
Figure 6 On-Resistance Variation with Temperature



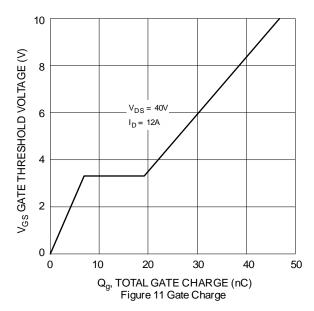


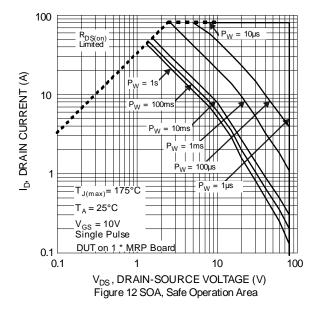


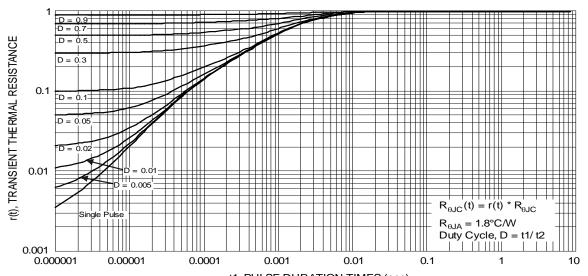












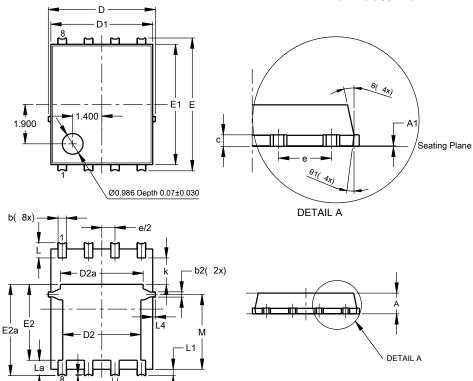
t1, PULSE DURATION TIMES (sec) Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)

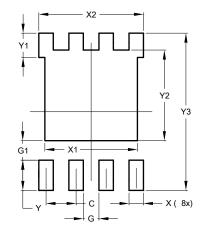


PowerDI5060-8 (SWP) (Type Q)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4).25REF			
С	0.230	0.330	0.277		
D		.15 BS0			
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	3.98			
E	6	.40 BS0	2		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е		.27BSC)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value		
Dimonorono	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		

June 2017



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